

# Curriculum Vitae

## Cheng Wang

Assistant Professor  
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### Professional Employment

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<b>Assistant Professor</b> <i>Iowa State University</i>	2022 - Present Ames, IA
<b>Research Scientist</b> <i>Purdue University</i>	2019 – 2022 West Lafayette, IN
<b>Research and Development Engineer</b> <i>Seagate Technology</i>	2016 – 2019 Fremont, CA

### Education

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Ph.D. Physics <i>The University of Texas at Austin</i>	2010 - 2015 Austin, TX
B.S. Physics <i>Peking University</i>	2005 - 2009 Beijing, China

### Current Research

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**Design energy-efficient hardware acceleration for machine learning (ML) through co-design across the stack of device-circuit, architecture, and algorithm**, with a particular emphasis on **Computing In Memory (CIM)** based on **emerging non-volatile memories (NVMs)**. Develop novel electronic devices and systems for **emerging non-volatile memory and high-density data storage**.

**Improve efficiency** of processing **artificial intelligence (AI)** and **brain-inspired computational models** by exploiting various **emerging electronic/photonic devices and materials**.

**Explore novel algorithms** in pursuit of efficient processing of ML tasks (such as computer vision and sequential processing) geared for **resource-constrained scenarios such as edge applications**.

### Previous Research Experience

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<b>Research Scientist</b> <b>Center for Brain Inspired Computing (C-BRIC), Purdue University</b> – Center Director: Professor Kaushik Roy	2019-2022 West Lafayette, IN
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- Explored emerging Spin-Orbit-Torque MRAM crossbars for **reliable ML inference hardware**. Conducted **sparsity-aware device-circuit-system co-design** to address the two main design challenges in analog in-memory computing – crossbar non-idealities and high latency/energy cost from analog-digital converters.
- Proposed a highly **scalable analog magnetic memory** based on **multi-domain quantum spin devices**. Observed **improved energy efficiency and noise resiliency with such neuro-mimetic hardware**.
- Conducted in-depth technology exploration of various leading NVM candidates for **building scalable crossbar-based in-memory computing system**. Integrated technology-aware array-level simulation and analysis of computational error and energy/area cost into system-level performance evaluation.

- Exploited MRAM for **ML training acceleration**. Investigated the design trade-off involving write voltage, latency, and error rate based on the device characteristics. Improved system-level performance by leveraging the inherent algorithm-level noise resiliency combined with a hardware-software co-design.
- Developed exploratory computational models and algorithms for complex AI tasks such as image or text processing. **Achieved significant energy and memory saving at sequential processing** using a novel **spectral domain** oscillatory recurrent neural network.

**Senior/Staff R&D Engineer, Seagate Technology**

2016-2019

**Optimized the device design for multi-bit memory**, and experimentally demonstrated highly scalable analog magnetic memory states based on commercial data storage platform.

**Proposed magnetic granular devices for analog in-memory computing**. Experimentally demonstrated highly scalable analog magnetic memory states based on commercial data storage platform.

**Recognition: Technical Award 2018** (Fremont Research Center)

**Graduate Research Assistant, UT Austin**

2010-2015

**Observed electrically tunable I-V characteristics with memristive switching** in an iridium (Ir)-based quantum material, paving the way of developing memristors based on novel oxides. Discovered sizeable anisotropic magnetoresistance in an antiferromagnetic (AF) oxide which for AF-based memory. Developed electrical detection of spin-transfer-torque driven ferromagnetic resonance (STT-FMR) for developing ultra-fast MRAM.

**Research Assistant, Institute of Physics, Chinese Academy of Sciences**

2009-2010

Developed device modeling of one-dimensional electron transport with current-driven magnetic domain wall motion in magneto-electronic memory devices.

## Selected Publications

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- **Cheng Wang**, Chankyu Lee, and Kaushik Roy, “**Noise resilient leaky integrate-fire neuron based on multi-domain spintronic devices**”, *Scientific Reports* 12 8361 (2022).
- Wilfried Haensch, Anand Raghunathan, Cheng Wang et al, “**A Co-design view of Compute in-Memory with Non-Volatile Elements for Neural Networks**”, in press, *Advanced Materials* (2022).
- Gobinda Saha, **Cheng Wang**, and Kaushik Roy, “**Invited: A Cross-layer Approach to Cognitive Computing**”, In press, *IEEE/ACM Design Automation Conference* (2022).
- Kang He, Indranil Chakraborty, **Cheng Wang** and Kaushik Roy, “**Design Space and Memory Technology Co-exploration for In-Memory Computing Based Machine Learning Accelerators**”, *IEEE/ACM International Conference on Computer-Aided Design (ICCAD)* (2022).
- Bing Han, **Cheng Wang**, and Kaushik Roy, “**Oscillatory-Fourier Neural Network: A Compact and Efficient Architecture for Sequential Processing**”, *Conference on Artificial Intelligence (AAAI 2022)*,
- Tanvi Sharma, **Cheng Wang**, Amogh Agrawal, and Kaushik Roy, “**Enabling Robust SOT-MTJ Crossbars for Machine Learning using Sparsity-Aware Device-Circuit Co-design**”. 2021 *IEEE/ACM International Symposium on Low Power Electronics and Design (ISLPED)*.
- Hussam Amrouch, **Cheng Wang**, et al “**Brain-Inspired Computing: Adventure from Beyond CMOS Technologies to Beyond von Neumann Architectures**”, *IEEE/ACM ICCAD 2021*.
- Amogh Agrawal, **Cheng Wang**, Tanvi Sharma, and Kaushik Roy, “**Magneto-resistive Circuits and Systems: Embedded Non-Volatile Memory to Crossbar Arrays**”, *IEEE Transactions on Circuits and Systems I*. 68, 6 (2021) Selected as Highlight of 2021 June Issue.